GSDSRB551V-30

Schottky Barrier Diode

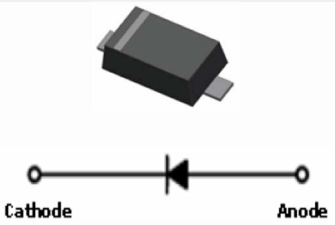
Product Description

Schottky Barrier Diode 200mW / 30V

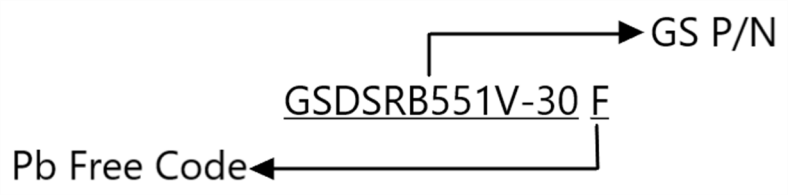
Features

- Low Forward Voltage Drop
- Flat Lead SOD-323 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicate Cathode

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit diagram
GSDSRB551V-30F	SOD-323	B3	

Ordering Information



Part Number	Package	Quantity
GSDSRB551V-30F	SOD-323	3000 PCS

Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	200	mW
V_{RM}	Repetitive Peak Reverse Voltage	30	V
V_R	Maximum DC Blocking Voltage	20	V
T_J	Operating Junction Temperature	+125	°C
T_{STG}	Storage Temperature Range	-65 to +125	°C
$I_{F(AV)}$	Average Forward Rectified Current	500	mA
I_{FSM}	Peak Forward Surge Current (At 8.3ms Single half sine-wave)	5	A

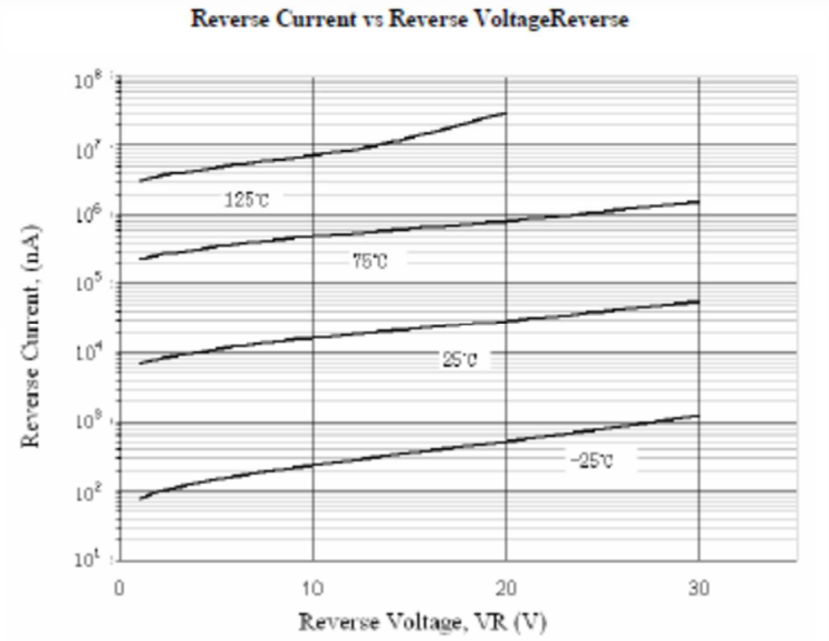
These ratings are limiting values above which the serviceability of the diode may be impaired.

Electrical Characteristics

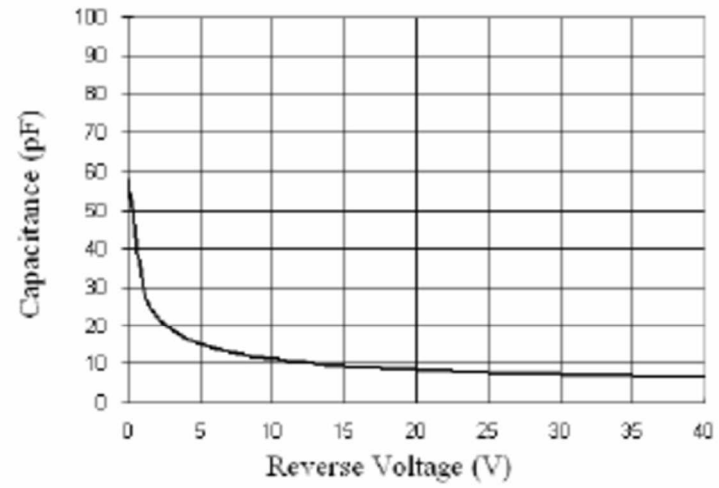
(T_A=25°C Unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Max	Unit
B_V	Breakdown Voltage	I_R =500μA	30	-	V
I_R	Reverse Leakage Current	V_R=20V	-	100	μA
V_F	Forward Voltage	I_F =100mA I_F =500mA	-	0.36 0.47	V

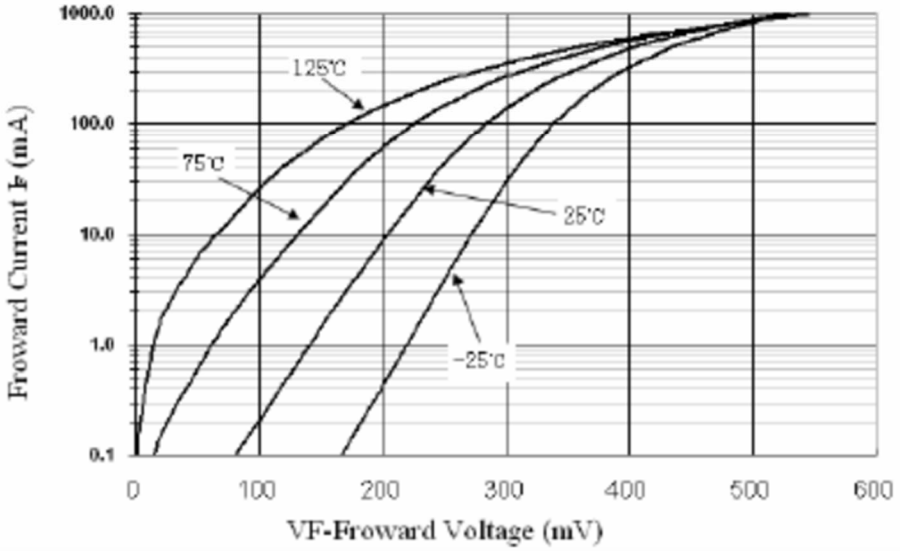
Typical Characteristics



Total Capacitance

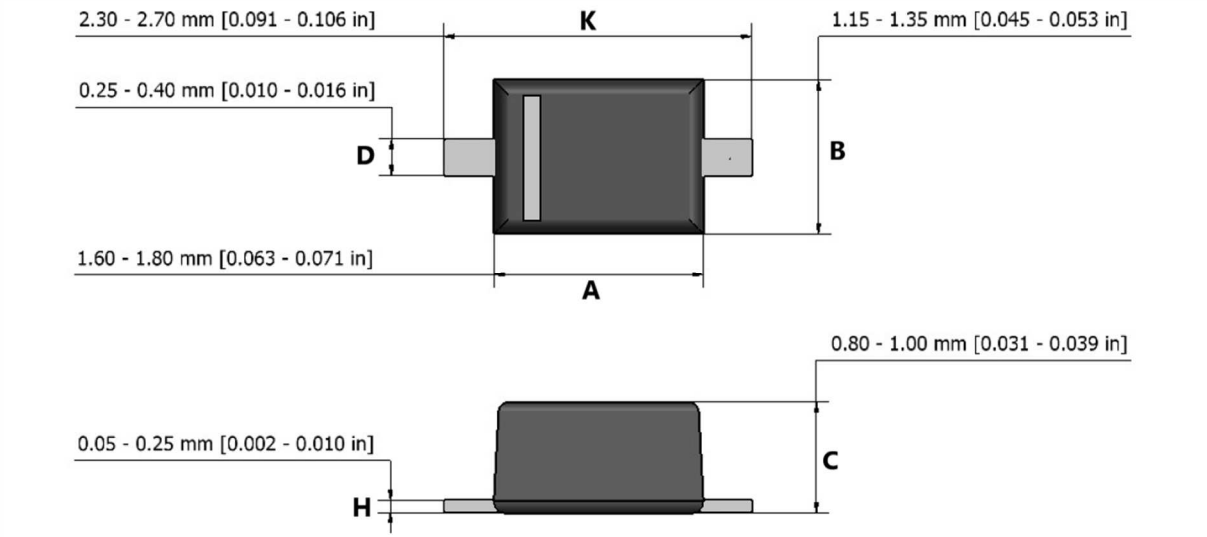


Forward Voltage vs Ambient Temperature



Package Dimension

SOD-323



NOTES:
1. The above package outline is similar to JEITA SC-90.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.6	1.8	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.8	1	0.031	0.039
D	0.25	0.4	0.01	0.016
H	0.05	0.25	0.002	0.01
K	2.3	2.7	0.091	0.106

Pin 1.CATHODE
Pin 2.ANODE

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